TOIREX

XP161A1355PR-G

ETR1124_003

Power MOSFET

■GENERAL DESCRIPTION

The XP161A1355PR-G is an N-channel Power MOSFET with low on-state resistance and ultra high-speed switching characteristics.

Because high-speed switching is possible, the IC can be efficiently set thereby saving energy.

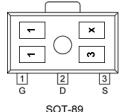
A gate protect diode is built-in to prevent static damage.

The small SOT-89 package makes high density mounting possible.

■ APPLICATIONS

- Notebook PCs
- Cellular and portable phones
- On-board power supplies
- Li-ion battery systems

■PIN CONFIGURATION/ MARKING

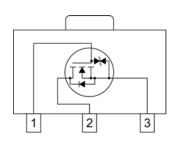


G : Gate S : Source

D : Drain

SOT-89 (TOP VIEW)

■EQUIVALENT CIRCUIT



N-channel MOSFET (1 device built-in)

■FEATURES

Low On-State Resistance : Rds (on)= 0.05Ω @ Vgs = 4.5V

: Rds (on)= 0.07Ω @ Vgs = 2.5V: Rds (on)= 0.15Ω @ Vgs = 1.5V

Ultra High-Speed Switching
Gate Protect Diode Built-in
Driving Voltage : 1.5V
N-Channel Power MOSFET

DMOS Structure

Small Package : SOT-89

Environmentally Friendly: EU RoHS Compliant, Pb Free

■PRODUCT NAME

PRODUCT NAME	PACKAGE	ORDER UNIT		
XP161A1355PR	SOT-89	1,000/Reel		
XP161A1355PR-G ^(*)	SOT-89	1,000/Reel		

^(*) The "-G" suffix denotes Halogen and Antimony free as well as being fully RoHS compliant.

■ ABSOLUTE MAXIMUM RATINGS

Ta = 25°C

PARAMETER	SYMBOL	RATINGS	UNITS
Drain-Source Voltage	Vdss	20	V
Gate-Source Voltage	Vgss	±8	V
Drain Current (DC)	ld	4	Α
Drain Current (Pulse)	Idp	16	Α
Reverse Drain Current	ldr	4	Α
Channel Power Dissipation *	Pd	2	W
Channel Temperature	Tch	150	°C
Storage Temperature	Tstg	-55~150	°C

^{*} When implemented on a ceramic PCB

^{*} x represents production lot number.

■ELECTRICAL CHARACTERISTICS

DC Characteristics Ta = 25°C

PARAMETER	SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	UNITS
Drain Cut-Off Current	ldss	Vds=20V, Vgs= 0V	-	-	10	μΑ
Gate-Source Leak Current	Igss	Vgs= ±8V, Vds= 0V	ı	ı	±10	μΑ
Gate-Source Cut-Off Voltage	Vgs(off)	Id= 1mA, Vds= 10V	0.5	ı	1.2	V
Orain-Source On-State Resistance *1	Rds(on)	Id= 2A, Vgs= 4.5V	ı	0.037	0.050	Ω
		Id= 2A, Vgs= 2.5V	ı	0.05	0.07	Ω
		Id= 0.5A, Vgs= 1.5V	ı	0.1	0.15	Ω
Forward Transfer Admittance *1	Yfs	ld= 2A, Vds= 10V	-	10	-	S
Body Drain Diode Forward Voltage	Vf	If= 4A, Vgs= 0V	-	0.85	1.1	٧

^{*1} Effective during pulse test.

Dynamic Characteristics

Ta = 25°C

PARAMETER	SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	UNITS
Input Capacitance	Ciss	Vds= 10V, Vgs=0V f= 1MHz		390		pF
Output Capacitance	Coss		-	210	-	pF
Feedback Capacitance	Crss		-	90	-	pF

Switching Characteristics

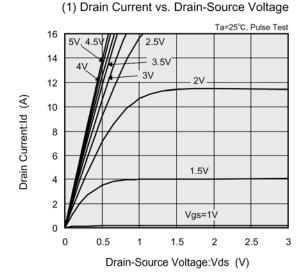
Ta = 25°C

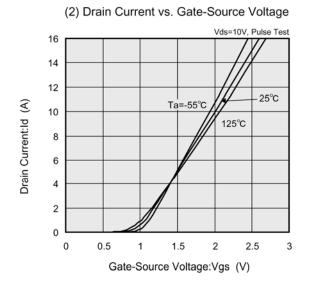
PARAMETER	SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	UNITS
Turn-On Delay Time	td (on)	Vgs= 5V, Id=2A Vdd= 10V	ı	10	ı	ns
Rise Time	tr		ı	15	ı	ns
Turn-Off Delay Time	td (off)		-	85		ns
Fall Time	tf		-	45	-	ns

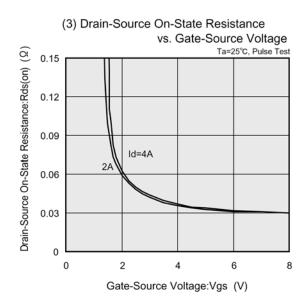
Thermal Characteristics

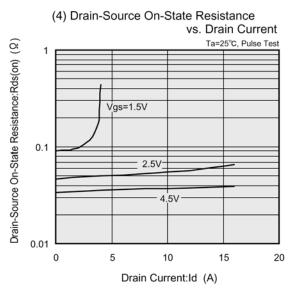
PARAMETER	SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	UNITS
Thermal Resistance (Channel-Ambience)	Rth (ch-a)	Implement on a ceramic PCB	-	62.5	-	°C/W

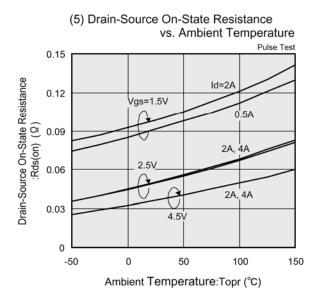
■TYPICAL PERFORMANCE CHARACTERISTICS

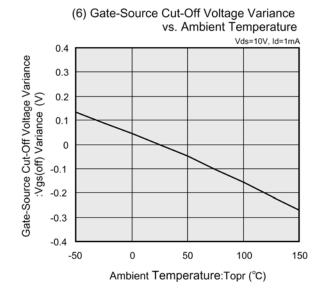






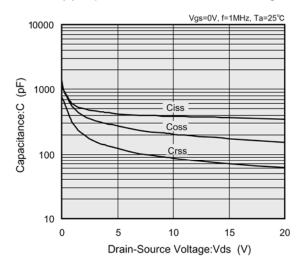




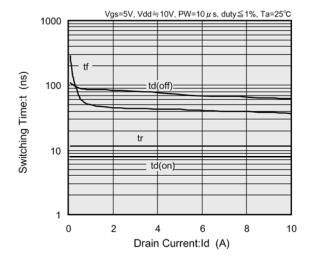


■TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

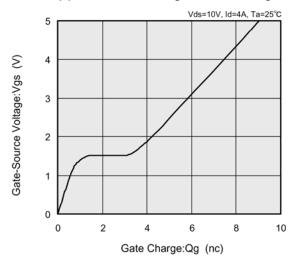




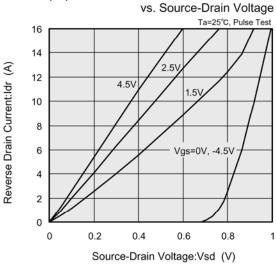
(8) Switching Time vs. Drain Current



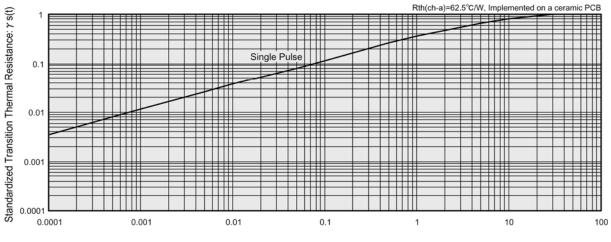
(9) Gate-Source Voltage vs. Gate Charge



(10) Reverse Drain Current



(11) Standardized transition Thermal Resistance vs. Pulse Width



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